

Amendments to the Specification

Please replace the title as follows:

METHOD OF FORMING THIN FILM PATTERNING SUBSTRATE INCLUDING
FORMATION OF BANKS AND SURFACE TREATMENT THEREFOR

Please add the following paragraph between the title and the first line of text as follows:

This is a Continuation of Application No. 09/423,969 filed November 17, 1999, which in turn is a U.S. National Stage of PCT/JP99/01327 filed March 17, 1999. The entire disclosure of the prior applications is hereby incorporated by reference herein in its entirety.

Please replace the paragraph beginning on page 30, line 24, with the following rewritten paragraph:

A first, second, and third embodiment of the present invention, ~~as cited in claims 1-29~~, together with modification examples therefor, are now described.

Please replace the paragraph beginning on page 46, line 24, with the following rewritten paragraph:

Next, the second interlayer insulating film 52 is formed and a contact hole is formed in this interlayer insulating film in the portion corresponding to the relay electrode 35. Next, after forming an ITO film over the entire surface of the second interlayer insulating film 52, patterning is performed, and a pixel electrode 4142 is formed, for each pixel 7, electrically connected to the source-drain region in the second TFT 30 via the contact hole.

Please replace the paragraph beginning on page 53, line 20, with the following rewritten paragraph:

Fourth to seventh embodiments, and modification examples thereof, are now described ~~which embody the inventions cited in claims 30-48~~.

Please replace the paragraph beginning on page 75, line 24, with the following rewritten paragraph:

The bank layer BANK is formed along the data line SIG and the scanning lines GATE, thicker than the organic semiconductor film 4341, and thereon is formed the opposing electrode OP. Therefore, due to the presence of the bank layer BANK, large capacitances can be prevented from becoming parasitic on the data line SIG. That is, because the thick bank layer BANK is also interposed between the data line SIG and the opposing electrode OP, the parasitic capacitance produced in the data line SIG is extremely small. Because of that fact, the loads on the drive circuits 3 and 4 can be reduced, and it becomes possible to effect low power consumption operation and/or faster display operations.

Please replace the paragraph beginning on page 76, line 23, with the following rewritten paragraph:

If such a two-layer structure is effected, moreover, the organic semiconductor film 4341 comes in contact with the lower layer side insulating film made of the inorganic material, but it does not come in contact with the upper layer side insulating film 62 made of the organic material. Because of that, the organic semiconductor film 4341 will not deteriorate under the influence of the upper layer side insulating film 62 configured of the organic material, wherefore, in the thin film light emitting element 40, there is no decline in either light emitting efficiency or reliability.

Please replace the paragraph beginning on page 81, line 5, with the following rewritten paragraph:

Lower layer side insulating film formation process (Fig. 16A- 16C): Next, a film (an inorganic film for forming the lower layer side insulating film 61) consisting of an inorganic material is formed in a PECVD process or the like on the front surface of the second interlayer insulating film 52. This film is formed of the inorganic material and to the

thickness described in the embodying aspect described earlier. This film is formed to a thickness that is greater than the thickness of the organic semiconductor film 4341. If the organic semiconductor film 41 is formed to a thickness of 0.05 μm to 0.2 μm , for example, the film of inorganic material is formed to a thickness of approximately 0.2 μm to 1.0 μm .

Please replace the paragraph beginning on page 81, line 17, with the following rewritten paragraph:

Upper layer side insulating film formation process (Fig. 17A - 17C): A resist (upper layer side insulating film 62) is then formed along the scanning line GATE and the data line SIG. This upper layer side insulating film 62 is configured of the organic material of the embodying aspect described earlier. The thickness of the upper layer side insulating film 62 is formed to a height wherewith it can become a bulwark of such extent that the liquid thin film material will not overflow into the adjacent pixel areas even when the pixel area is filled with the liquid thin film material. If the organic semiconductor film 4341 is formed to a thickness of 0.05 μm to 0.2 μm , or example, the upper layer side insulating film 62 is formed to a height of 1 μm to 2 μm or so.

Please replace the paragraph beginning on page 86, line 11, with the following rewritten paragraph:

The inventions described in claims 31-39 are not limited to or by the fourth to seventh embodiments, but can be applied in various modifications within the scope of the essential invention.

Please replace the paragraph beginning on page 88, line 18, with the following rewritten paragraph:

The invention inventions described in claims 49 to 74 are next described in eighth to 11th embodiments, making reference to the drawings.